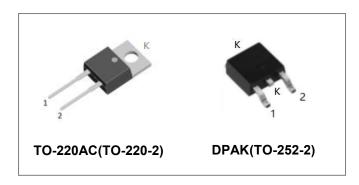






S4D02120A S4D02120E 1200V SIC POWER SCHOTTKY RECTIFIERS



Description

This 1200V 2A diode is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D02120A/S4D02120E are ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- · Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- · Switching supply output rectification
- Reverse polarity protection







Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	1200	V
Average Rectified Forward Current	l _{F (AV)1}	Tc=25°C	9	A
	I _{F (AV)2}	Tc=160°C	2	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM1}	10ms, Half Sine pulse, Tc =25°C	27	А
	I _{FSM2}	10ms, Half Sine pulse, Tc =110°C	25	Α
Repetitive Peak Forward Surge Current	I_{FRM1}	10ms, Half Sine pulse , Tc =25°C	16	А
	I_{FRM2}	10ms, Half Sine pulse , Tc =110°C	14	А
Non-Repetitive Peak Forward Surge Current	I _{F,Max1}	10μs. Pulse, Tc=25°C	200	Α
	I _{F,Max2}	10μs. Pulse, Tc=110°C	160	А
Power Dissipation	P _{tot1}	Tc=25℃	60	W
	P _{tot2}	Tc=110°C	26	W

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 2A, Pulse, T _J = 25 °C	1.4	1.8	V
	V_{F2}	@ 2A, Pulse, T _J = 175 °C	2.0	2.5	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25 ^{\circ}C$	1	10	uA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 175 ^{\circ}\text{C}$	2	40	uA
Junction Capacitance	Ст	VR=0V, Tj=25℃,f=1MHz	160	-	pF
Reverse Recovery Charge	Qc	I_F = 2A, di/dt = 200A/ μ s VR = 800 V, T $_J$ =25°C	12.33	-	nC
Capacitance Stored Energy	Ec	V _R = 800 V, T _J =25°C	6.33	-	μJ

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	S4D02120A	S4D02120E	Units	
Junction Temperature	TJ	-55 to +175		°C	
Storage Temperature	T _{stg}	-55 to +175		°C	
Typical Thermal Resistance Junction to Case	R _{qJC}	2.4	2.5	°C/W	

Ordering Information

Device	Package	Shipping
S4D02120A	TO-220AC(TO-220-2)	50pcs / tube
S4D02120E	DPAK(TO-252-2)	2500pcs / reel
S4D02120ETR	DPAK(TO-252-2)	2500pcs / reel

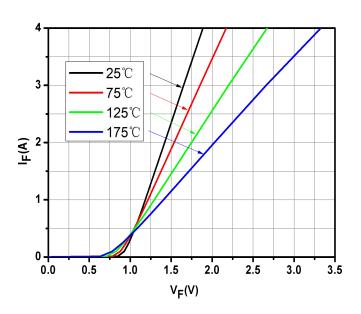
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.







Ratings and Characteristics Curves



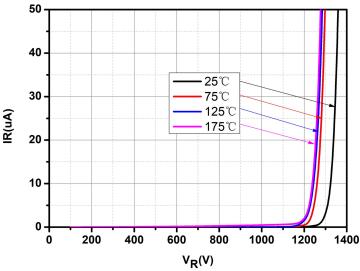
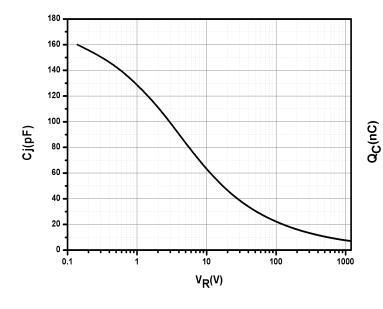


Fig.1-Typical Forward Voltage Characteristics





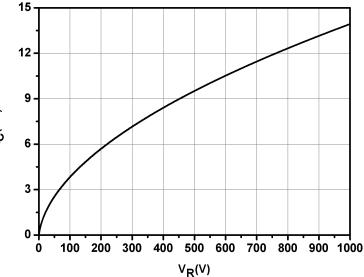


Fig.3-Capacitance vs. Reverse Voltage

Fig.4-Total Capacitance Charge vs. Reverse Voltage







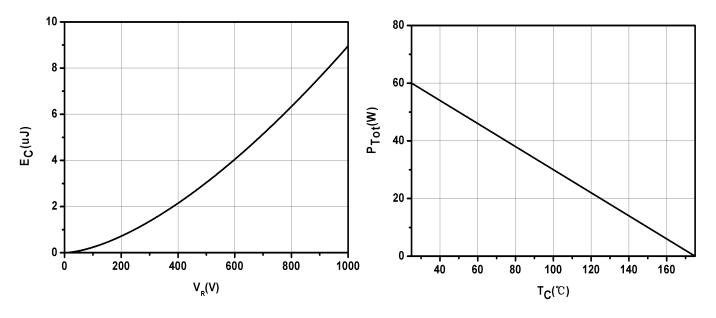


Fig.5-Capacitance Stored Energy

Fig.6-Power Derating

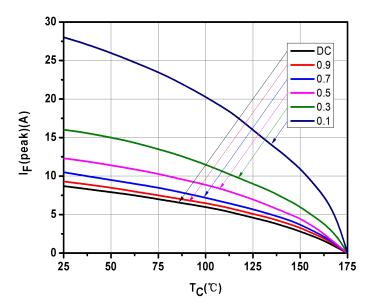


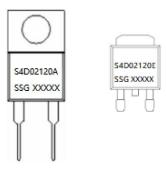
Fig.7-Current Derating







Marking Diagram



Where XXXXX is YYWWL

 S4D
 = Device Type

 A/E
 = Package type

 02
 = Forward Current (2A)

 120
 = Reverse Voltage (1200V)

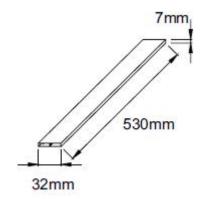
 SSG
 = SSG

YY = Year
WW = Week
L = Lot Number

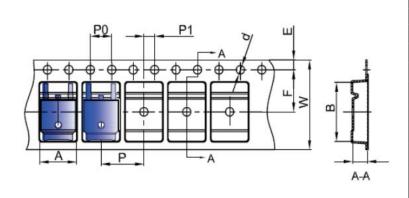
Cautions: Molding resin

Epoxy resin UL:94V-0

Tube Specification(TO-220-2)



Carrier Tape & Reel Specification DPAK(TO-252-2)



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

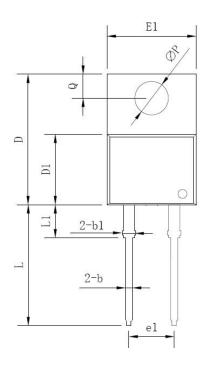
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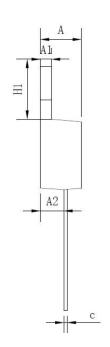






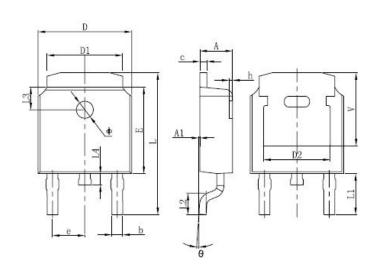
Mechanical Dimensions TO-220AC(TO-220-2)





Symbol	Dimensions in millimeters			
,	Min.	Typical	Max.	
Α	3.56	-	4.83	
A1	0.51	-	1.40	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
С	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E1	9.65	10.16	10.67	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.70	-	14.73	
L1	-	-	6.35	
ФР	-	3.56	-	
Q	2.54	-	3.43	

Mechanical Dimensions DPAK(TO-252-2)



SYMBOL	Dimensions in millimeters			
	Min.	Тур.	Max.	
А	2.18	-	2.39	
A1	•	-	0.13	
b	0.64	-	0.89	
С	0.46	-	0.89	
D	6.35	-	6.73	
D1	4.95	-	5.46	
D2	4.32	-	-	
E	5.97	6.1	6.22	
е	2.29BSC			
L	9.4	-	10.41	
L1	2.90 REF.			
L2	1.4	1.52	1.78	
L3	1.60 REF.			
L4	-	-	1.02	
Ф	1.1	-	1.3	
Θ	0°	-	10°	
V	5.21	_	-	

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